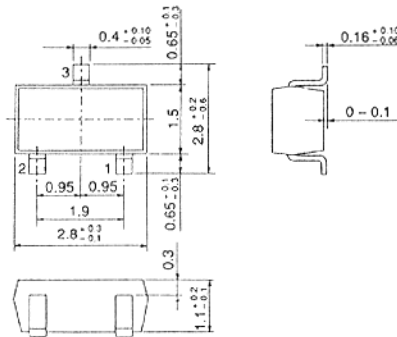


2SA1171

SILICON PNP EPITAXIAL

LOW FREQUENCY SMALL SIGNAL AMPLIFIER



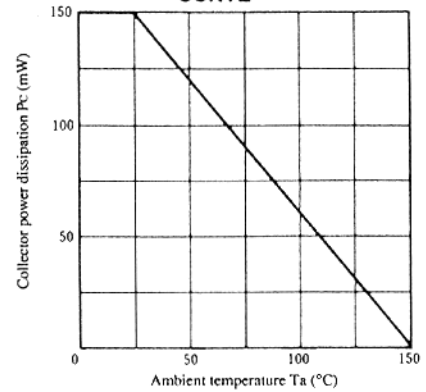
1. Emitter
 2. Base
 3. Collector
- (Dimensions in mm)

(MPAK)

■ ABSOLUTE MAXIMUM RATINGS (Ta=25°C)

Item	Symbol	2SA1171	Unit
Collector to base voltage	V _{CB0}	-90	V
Collector to emitter voltage	V _{CE0}	-90	V
Emitter to base voltage	V _{EB0}	-5	V
Collector current	I _C	-50	mA
Collector power dissipation	P _C	150	mW
Junction temperature	T _J	150	°C
Storage temperature	T _{stg}	-55 to +150	°C

MAXIMUM COLLECTOR DISSIPATION CURVE



■ ELECTRICAL CHARACTERISTICS (Ta=25°C)

Item	Symbol	Test Condition	min.	typ.	max.	Unit
Collector to emitter breakdown voltage	V _{(BR)CEO}	I _C = -1mA, R _{BE} = ∞	-90	—	—	V
Collector cutoff current	I _{CBO}	V _{CB} = -75V, I _E = 0	—	—	-0.5	μA
DC current transfer ratio	h _{FE} *	V _{CE} = -12V, I _C = -2mA	250	—	800	
Base to emitter voltage	V _{BE}	V _{CE} = -12V, I _C = -2mA	—	—	-0.75	V
Collector to emitter saturation voltage	V _{CE(sat)}	I _C = -10mA, I _B = -1mA	—	—	-0.5	V
Gain bandwidth product	f _T	V _{CE} = -12V, I _C = -2mA	—	200	—	MHz
Collector output capacitance	C _{ob}	V _{CE} = -25V, I _E = 0, f = 1MHz	—	1.6	—	pF

* The 2SA1171 is grouped by h_{FE} as follows.

Grade	D	E
Mark	PD	PE
h _{FE}	250 to 500	400 to 800

■ See characteristic curves of 2SA872.